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=> fil reg
FILE 'REGISTRY' ENTERED AT 10:33:23 ON 05 MAR 2010
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STRUCTURE FILE UPDATES:    3 MAR 2010  HIGHEST RN 1207829-36-4
DICTIONARY FILE UPDATES:   3 MAR 2010  HIGHEST RN 1207829-36-4

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TSCA INFORMATION NOW CURRENT THROUGH June 26, 2009.

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http://www.cas.org/support/stngen/stndoc/properties.html

=> d que
L2            20 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  (1333-74-0/BI OR
                 15318-08-8/BI OR 19553-62-9/BI OR 20791-15-5/BI OR
                 310888-77-8/BI OR 310888-80-3/BI OR 310888-81-4/BI OR
                 310888-82-5/BI OR 310888-85-8/BI OR 310888-87-0/BI OR
                 7358-26-1/BI OR 7440-37-1/BI OR 7440-59-7/BI OR 75-24-1/BI
                 OR 7727-37-9/BI OR 870126-56-0/BI OR 870126-57-1/BI OR
                 870126-58-2/BI OR 870126-59-3/BI OR 97-93-8/BI)
L7          1182 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  C19H14N2O2/MF
L9            24 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L7 AND 8-QUIN?
L10           11 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L9 AND QUINOLINOL
                 ?
L11           10 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L10 NOT
                 1H-INDOLE?
L12            1 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  8-HYDROXYQUINOLIN
                 ATE/CN
L13            1 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  8-HYDROXYQUINOLIN
                 E/CN
L14          685 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  148-24-3/CRN
L21            2 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  63969-39-1/CRN
L25           34 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  2536-71-2/CRN
L26       664194 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  (AL OR GA OR
                 ZN)/ELS
L27       122588 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L26 AND CCS/CI
L28       541606 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L26 NOT L27
L29       541606 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L28 OR L28
L30       300000 SEA FILE=REGISTRY RAN=(173475-42-8) SPE=ON  ABB=ON  PLU=ON
                  L28 OR L28
L31       241606 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L29 NOT L30
L32           30 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L12
L33        10124 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L13
L34         1839 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L14
L35            3 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L21
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L36           7 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L25
L37          60 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L11
L38      143270 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L27
L39      140282 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L30
L40     2256613 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L31
L41        2571 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  (L32 OR L33 OR
                L34 OR L35 OR L36 OR L37) AND (L38 OR L39 OR L40)
L42             QUE  SPE=ON  ABB=ON  PLU=ON  CHEMICAL VAPOR DEPOSIT? OR C
                HEMICAL VAPOUR DEPOSIT? OR CVP OR VAPOR DEPOSIT? OR VAPOU
                R DEPOSIT?
L43          27 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L41 AND L42
L44      247082 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  "VAPOR DEPOSITION
                PROCESS"+PFT,NT/CT
L45          28 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L41 AND L44
L46          31 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L43 OR L45
L47             QUE  SPE=ON  ABB=ON  PLU=ON  FILM? OR THINFILM? OR LAYER?
                 OR OVERLAY? OR OVERLAID? OR LAMIN? OR LAMEL? OR (MULTILA
                YER?) OR SHEET? OR LEAF? OR FOIL? OR COAT? OR TOPCOAT? OR
                 OVERCOAT? OR VENEER? OR SHEATH? OR COVER? OR ENVELOP? OR
                 ENCAS? OR ENWRAP? OR OVERSPREAD?
L48          30 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L46 AND L47
L49         130 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  (L32 OR L33 OR
                L34 OR L35 OR L36 OR L37)(5A)L47
L50           5 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L49 AND L42
L51           5 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L50 AND L41
L52          30 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L48 OR (L50 OR
                L51)
L53          18 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L52 AND (1840-2006
                )/PRY,AY,PY
L54         565 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L41 AND L47
L55          27 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L54 AND L44
L57          16 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L55 AND (1840-2006
                )/PRY,AY,PY
L58          16 SEA FILE=REGISTRY SPE=ON  ABB=ON  PLU=ON  L2 AND M/ELS
L59       23254 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L58
L60        1415 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L59 AND L42
L61        1210 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L60 AND L47
L62           1 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L61 AND (L32 OR
                L33 OR L34 OR L35 OR L36 OR L37)
L63           1 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L60 AND (L32 OR
                L33 OR L34 OR L35 OR L36 OR L37)
L64          49 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L59 AND (L32 OR
                L33 OR L34 OR L35 OR L36 OR L37)
L65           1 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L64 AND L42
L66          19 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L53 OR L62 OR L63
                OR L65
L68          19 SEA FILE=HCAPLUS SPE=ON  ABB=ON  PLU=ON  L66 OR L57


=> fil hcap
FILE 'HCAPLUS' ENTERED AT 10:33:29 ON 05 MAR 2010
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FILE COVERS 1907 - 5 Mar 2010 VOL 152 ISS 11
FILE LAST UPDATED: 4 Mar 2010 (20100304/ED)
REVISED CLASS FIELDS (/NCL) LAST RELOADED: Dec 2009
USPTO MANUAL OF CLASSIFICATIONS THESAURUS ISSUE DATE: Dec 2009

HCAplus now includes complete International Patent Classification (IPC) reclassification data for the third quarter of 2009.

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This file contains CAS Registry Numbers for easy and accurate substance identification.

=> d l68 1-19 ibib ed abs hitstr hitind

L68 ANSWER 1 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2008:1127854 HCAPLUS Full-text
DOCUMENT NUMBER: 149:366841
TITLE: Atomic layer chemical vapor deposition with in situ synthesis of molecular metalorganic compounds and uses of the resulting films
INVENTOR(S): Nilsen, Ola; Fjellvaag, Helmer
PATENT ASSIGNEE(S): Universitetet I Oslo, Norway
SOURCE: PCT Int. Appl., 25pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2008111850	A2	20080918	WO 2008-NO99	20080314
WO 2008111850	A3	20090129		

W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AP, EA, EP, OA

PRIORITY APPLN. INFO.: NO 2007-1400 A 20070315

ED Entered STN: 19 Sep 2008

AB Methods for preparing thin films comprising mol. metalorg. compds. on a substrate using an atomic layer gas phase deposition technique are described which entail contacting the substrate with a pulse of an inorg. precursor selected from a group consisting of metal alkyls, metal cycloalkyls, metal aryls, metal amines, metal silylamines, metal halogenides, metal carbonyls, and metal chelates; reacting the inorg. precursor with an organic compound present on at least one surface of the substrate or adsorbing the inorg. precursor on at least one surface of the substrate; removing any nonadsorbed or unreacted inorg. precursors and reaction byproducts; contacting the inorg. precursor on the surface of the substrate with a pulse of an organic precursor with at least one functional group capable of a chemical reaction with an inorg. precursor; reacting the organic precursor with the inorg. compound adsorbed on the surface or adsorbing the organic precursor; removing any nonadsorbed or unreacted organic precursors; and optionally repeating the preceding steps until a desired film thickness is achieved. A layer of metalorg. compds. is formed in either one of the reaction steps. The metal is selected from Al, Ga, In, Tl, Si, Ge, Sn, Pb, As, Sb, Bi, Te, Po, alkali metals, alkaline earth metals, 3d metals, 4d metals, 5d metals, lanthanides, and actinides. Substrates provided with the films are also described, as is the use of the films as a semiconductive material in organic light-emitting device applications (including displays).

IT 75-24-1, Trimethylaluminum 148-24-3, 8-Hydroxyquinoline, processes
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

RN 75-24-1 HCAPLUS

CN Aluminum, trimethyl- (CA INDEX NAME)

RN 148-24-3 HCAPLUS

CN 8-Quinolinol (CA INDEX NAME)

CC 75-1 (Crystallography and Liquid Crystals)
Section cross-reference(s): 73, 74, 76, 78

ST atomic layer chem vapor deposition metalorg compd film; electroluminescent device display atomic layer CVD metalorg film

IT Silanes
(amino, metal compds.; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Semiconductor films
(atomic layer chemical vapor

deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Actinide compounds
Alkali metal compounds
Alkaline earth compounds
Rare earth compounds
Transition metal compounds
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Carbonyl complexes
Coordination compounds
Halides
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Chemical vapor deposition
(atomic layer; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Electroluminescent devices
(displays, organic; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Luminescent screens
(electroluminescent, organic; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Amines, processes
(metal compds.; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Electroluminescent devices
(organic; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT Amines, processes
(silyl, metal compds.; atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT 7439-92-1DP, Lead, compds. 7440-08-6DP, Polonium, compds. 7440-21-3DP, Silicon, compds. 7440-28-0DP, Thallium, compds. 7440-31-5DP, Tin, compds. 7440-36-0DP, Antimony, compds. 7440-38-2DP, Arsenic, compds. 7440-55-3DP, Gallium, compds. 7440-56-4DP, Germanium, compds. 7440-69-9DP, Bismuth, compds. 7440-74-6DP, Indium, compds. 13494-80-9DP, Tellurium, compds.
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT 555-32-8P 2085-33-8P, Tris(8-hydroxyquinolinato)aluminum 13978-85-3P, Bis(8-hydroxyquinolinato)zinc 17500-80-0P
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT 7732-18-5, Water, processes 10028-15-6, Ozone, processes
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

IT 65-85-0, Benzoic acid, processes 75-24-1, Trimethylaluminum 148-24-3, 8-Hydroxyquinoline, processes

557-20-0, Diethylzinc 7439-89-6D, Iron, compds. 7439-95-4D, Magnesium, compds. 7439-96-5D, Manganese, compds. 7440-06-4D, Platinum, compds. 7440-47-3D, Chromium, compds. 7440-48-4D, Cobalt, compds. 7440-50-8D, Copper, compds. 7440-62-2D, Vanadium, compds. 7550-45-0, Titanium tetrachloride, processes
(atomic layer chemical vapor deposition with in situ synthesis of mol. metalorg. compds. and uses of resulting films)

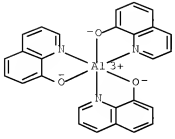
L68 ANSWER 2 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2008:379801 HCAPLUS Full-text
DOCUMENT NUMBER: 148:415641
TITLE: Transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element
INVENTOR(S): Tateishi, Tomomi
PATENT ASSIGNEE(S): Fujifilm Corporation, Japan
SOURCE: U.S. Pat. Appl. Publ., 25 pp.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20080075921	A1	20080327	US 2007-902031 <--	20070918
JP 2008084701	A	20080410	JP 2006-263437 <--	20060927
PRIORITY APPLN. INFO.:			JP 2006-263437 A <--	20060927

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 28 Mar 2008
AB The present invention provides a transfer material with a strong adhesiveness for an electronic device that includes a transfer support and, provided on the support in this order, an insulating layer or a partition wall material layer, and a layer containing an organic low-mol.-weight compound having charge transportability; a method of forming an insulating layer and a partition wall of an electronic device using the transfer material; and a light-emitting element.
IT 148-24-3D, 8-Quinolinol, derivs. 2085-33-8, Alq3
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 2085-33-8 HCAPLUS

CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



INCL 428141000; 156230000; 428172000
CC 76-3 (Electric Phenomena)
Section cross-reference(s): 48, 73
ST transfer electronic device insulating layer partition wall
LED fabrication
IT Cluster ions
(beams; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Anhydrides
(dianhydrides; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Vapor deposition process
(ion plating; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Materials
(organic; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Chemical vapor deposition
(photochem.; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Polymerization
Vapor deposition process
(plasma; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Acrylic polymers
(polysiloxane-, US-3700; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Conducting polymers
(polythiophenes; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)
IT Chemical vapor deposition
Coating process
Dielectric films
Electroluminescent devices
Holders

Molecular beam epitaxy
Reactive sputtering
Release films
Semiconductor device fabrication
Sputtering
Transfers
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

IT Metallophthalocyanines
Polyanilines
Polyesters
Polyphenyls
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

IT Vapor deposition process
(vacuum; transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

IT 67-63-0, Isopropyl alcohol, processes 78-93-3, Methyl ethyl ketone, processes 108-88-3, Toluene, processes 58328-31-7 60676-86-0, Vitreous silica 475644-38-3, Optool DSX 757974-86-0, TFR-H
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

IT 50926-11-9, Indium tin oxide 128770-43-4, HP 320 (polyester)
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

IT 90-44-8D, Anthrone, derivs. 92-52-4D, Biphenyl, quinone derivs. 147-14-8, Copper phthalocyanine 148-24-3D, 8-Quinolinol, derivs. 151-51-9D, Carbodiimide, derivs. 273-53-0D, Benzoxazole, metal complexes 288-42-6D, Oxazole, derivs. 288-88-0D, 1H-1,2,4-Triazole, derivs. 486-25-9D, Fluorenone, derivs. 574-93-6D, Phthalocyanine, derivs. 2085-33-8, Alq3 4425-82-5D, Fluorenylidenemethane, derivs. 7789-24-4, Lithium fluoride, processes 11120-54-0D, Oxadiazole, derivs. 12597-68-1, Stainless steel, processes 14990-02-4D, derivs. 25038-59-9, Lumirror T-60, processes 60475-00-5D, Thiopyran, derivs. 70359-39-6D, derivs. 95270-88-5D, Polyfluorene, derivs. 96638-49-2D, Polyphenylenevinylene, derivs. 123847-85-8 380234-99-1, ZPN 1100 693794-98-8
(transfer material for electronic device, method of forming insulating layer and partition wall of electronic device, and light-emitting element)

OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS)

L68 ANSWER 3 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2007:970780 HCAPLUS Full-text
DOCUMENT NUMBER: 147:332672
TITLE: Blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices
INVENTOR(S): Kathirgamanathan, Poopathy; Ganeshamurugan, Subramaniam; Kumaraverl, Muttulingham; Partheepan, Arumugam; Paramaswara, Gnanamoly
PATENT ASSIGNEE(S): Merck Patent GmbH, Germany
SOURCE: U.S. Pat. Appl. Publ., 29 pp., Cont.-in-part of

Appl. No. PCT/GB06/000441.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 4
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20070200096	A1	20070830	US 2007-732313 <--	20070403
WO 2000032717	A1	20000608	WO 1999-GB4024 <--	19991201
W: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, US, UZ, VN, YU, ZA, ZW				
RW: GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
WO 2003046107	A1	20030605	WO 2002-GB5268 <--	20021122
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US 20050106412	A1	20050519	US 2004-496416 <--	20040522
US 20060003089	A1	20060105	US 2005-140338 <--	20050527
US 7597926	B2	20091006		
WO 2006087521	A1	20060824	WO 2006-GB441 <--	20060209
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RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				

PRIORITY APPLN. INFO.:		
GB 1998-26406 <--	A	19981202
WO 1999-GB4024 <--	W	19991201
US 2001-857300 <--	B3	20010601
GB 2001-28074 <--	A	20011123

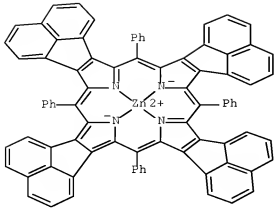
WO 2002-GB5268	W	20021122
<--		
US 2004-496416	A2	20040522
<--		
GB 2005-3393	A	20050218
<--		
US 2005-140338	A2	20050527
<--		
WO 2006-GB441	A2	20060209
<--		

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
OTHER SOURCE(S): MARPAT 147:332672
ED Entered STN: 31 Aug 2007
AB Electroluminescent composition is provided comprising (a) lithium quinolate or substituted quinolate exhibiting a blue electroluminescence and being the result of reaction between a lithium alkyl or alkoxide with 8-hydroxy quinoline or a substituted derivative thereof in a solvent which comprises acetonitrile and (b) a dopant. Also provided is an electroluminescent device which comprises sequentially (i) a first electrode (ii) a layer of an electroluminescent material which comprises lithium quinolate or substituted quinolate doped with a dopant and (iii) a second electrode.
IT 148-24-3, 8-Hydroxyquinoline, reactions
(blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

IT 21302-84-1 262280-95-5
(blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
RN 21302-84-1 HCAPLUS
CN 8-Quinolinol, zirconium(4+) salt (4:1) (CA INDEX NAME)

●1/4 Zr(IV)

RN 262280-95-5 HCAPLUS
CN Zinc, [8,17,26,35-tetraphenyl-37H,39H-tetraacenaphtho[1,2-b:1',2'-g:1'',2''-l:1''',2'''-q]porphinato(2-)-κN37,κN38,κN39,κN40]-, (SP-4-1)- (CA INDEX NAME)



IT 25387-93-3P
(doped electroluminescent material; blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
RN 25387-93-3 HCAPLUS
CN 8-Quinolinol, lithium salt (1:1) (CA INDEX NAME)

INCL 252301160; 313483000
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 25, 29, 76, 78
IT Vapor deposition process
(vacuum co-sublimation of lithium quinolate and dopant; blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
IT 109-04-6, 2-Bromopyridine 109-72-8, n-Butyllithium, reactions 148-24-3, 8-Hydroxyquinoline, reactions 1137-68-4, 2-2-Pyridyl-benzimidazole 10025-83-9, Iridium trichloride 98437-23-1
(blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
IT 147-14-8, Copper phthalocyanine 4733-39-5, BCP 21302-84-1 21392-78-9 262280-95-5
(blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
IT 25387-93-3P
(doped electroluminescent material; blue-emitting doped lithium

quinolate electroluminescent materials and related electroluminescent devices)
IT 7789-24-4, Lithium fluoride, uses
(electron injection layer; blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
IT 124729-98-2
(hole-transporting layer; blue-emitting doped lithium quinolate electroluminescent materials and related electroluminescent devices)
OS.CITING REF COUNT: 0 THERE ARE 0 CAPLUS RECORDS THAT CITE THIS RECORD (0 CITINGS)

L68 ANSWER 4 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2007:485383 HCAPLUS Full-text
DOCUMENT NUMBER: 146:473281
TITLE: Method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source
INVENTOR(S): Werner, Ansgar; Leo, Karl; Boettcher, Horst; Woehrle, Dieter; Thiel, Carolin; Wark, Michael
PATENT ASSIGNEE(S): Novaled A.-G., Germany
SOURCE: PCT Int. Appl., 18pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: German
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2007048624	A1	20070503	WO 2006-EP10368 <--	20061027
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GI, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
EP 1783846	A1	20070509	EP 2005-23595 <--	20051028
EP 1783846	B1	20080709		
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, AL, BA, HR, MK, YU				
JP 2009514152	T	20090402	JP 2008-537009 <--	20061027
KR 2008073306	A	20080808	KR 2008-712659 <--	20080527
PRIORITY APPLN. INFO.:			EP 2005-23595 A <--	20051028
			WO 2006-EP10368 W <--	20061027

ED Entered STN: 04 May 2007

AB The invention relates to a method for producing a layer consisting of a doped organic material on a substrate by means of deposition, the doped organic material containing at least one matrix material and at least one doping material. The inventive method is characterized in that a mixture of the matrix material and the doping material in a common evaporation source is transformed into a vapor phase and deposited onto the substrate, at least one of the matrix material or the doping material being inserted into a porous carrier substance before being transformed into the vapor phase. The invention also relates to the use of l such method.

IT 1344-28-1, Alumina, uses 7784-30-7, Aluminum phosphate
(matrix material; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)

RN 1344-28-1 HCAPLUS
CN Aluminum oxide (Al2O3) (CA INDEX NAME)

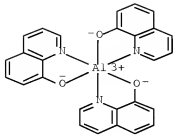
*** STRUCTURE DIAGRAM IS NOT AVAILABLE ***

RN 7784-30-7 HCAPLUS
CN Phosphoric acid, aluminum salt (1:1) (CA INDEX NAME)

IT 148-24-3, 8-Oxyquinoline, uses 2085-33-8, Alq3
(method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)

RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



CC 76-2 (Electric Phenomena)
Section cross-reference(s): 52, 73
ST vapor deposition doped org material solar cell electroluminescent device
IT Sol-gel processing
(coating; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT Molecular sieves
(matrix material; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT Zeolites (synthetic)
(matrix material; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT Doping
Hybrid organic-inorganic materials
Vapor deposition process
(method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT Electric conductors
Electroluminescent devices
Materials
Solar cells
(organic; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT Coating process
(sol-gel; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT 1314-23-4, Zirconia, uses 1344-28-1, Alumina, uses 7631-86-9, Silica, uses 7784-30-7, Aluminum phosphate 12736-95-7, Aluminum phosphate silicate 13463-67-7, Titania, uses
(matrix material; method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
IT 148-24-3, 8-Oxyquinoline, uses 517-51-1, Rubrene 2085-33-8, Alq3
(method for producing a layer consisting of doped organic material on a substrate by means of deposition from a common evaporation source)
OS.CITING REF COUNT: 2 THERE ARE 2 CAPLUS RECORDS THAT CITE THIS RECORD (2 CITINGS)

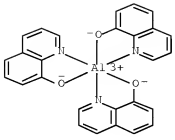
REFERENCE COUNT: 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 5 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2006:36976 HCAPLUS Full-text
DOCUMENT NUMBER: 144:117522
TITLE: Method of manufacturing organic thin film element, method of manufacturing electro-optic device, and method of manufacturing electronic equipment
INVENTOR(S): Takakuwa, Atsushi; Shimoda, Tatsuya; Furusawa, Masahiro; Mitani, Tadaoki; Yamaguchi, Hisato
PATENT ASSIGNEE(S): Seiko Epson Corporation, Japan; Tadaoki Mitani
SOURCE: U.S. Pat. Appl. Publ., 18 pp.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20060007520	A1	20060112	US 2005-141108 <--	20050601
JP 2006024535	A	20060126	JP 2004-203917 <--	20040709
PRIORITY APPLN. INFO.:			JP 2004-203917 A <--	20040709

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 13 Jan 2006
AB A method of manufacturing an organic thin film element including an organic thin film between a pair of thin film electrodes with ≥1 transparent electrode includes forming the transparent electrode by atomizing a material liquid containing a transparent-electrode forming material onto a base material; and forming the organic thin film on the transparent electrode. The organic thin film element is capable of simply providing an organic thin film element having a long element life. A method of manufacturing an electrooptic device as well as a method of manufacturing electronic equipment by using the above method are described.
IT 148-24-3, 8-Quinolinol, uses 2085-33-8, Tris(8-hydroxyquinolinato)aluminum
(organic film electrodes manufacturing with)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



INCL 359275000
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 22, 76
ST org film element electrooptic device electronic equipment manuf
IT Aromatic hydrocarbons, uses
(alkyl, polymers; organic film electrodes manufacturing with)
IT Amines, uses
Polyesters, uses
Polymers, uses
(aromatic; organic film electrodes manufacturing with)
IT Anhydrides
(heterocycle; organic film electrodes manufacturing with)
IT Film electrodes
(manufacturing with organic films)
IT Luminescence, electroluminescence
Spraying
Sputtering
(of organic film electrodes)
IT Self-assembled monolayers
(organic film electrodes manufacturing with)
IT Acrylic polymers, uses
Borate glasses
Borosilicate glasses
Coumarins
Glass, uses
Hydrazones
Phosphate glasses
Phosphosilicate glasses
Polyanilines
Polycarbonates, uses
Polyesters, uses
Polysilanes
Rare earth metals, uses
Silazanes
Silicate glasses
(organic film electrodes manufacturing with)
IT Films
(organic; electrodes manufacturing with)
IT Polysulfones, uses
(polyether-; organic film electrodes manufacturing with)
IT Polyethers, uses
(polysulfone-; organic film electrodes manufacturing with)
IT Conducting polymers
(polythiophenes; organic film electrodes manufacturing with)

IT Electrodes
(transparent; organic film electrodes manufacturing with)
IT Electronics
Electrooptical instruments
(using organic films)
IT 51-17-2, Benzimidazole 80-05-7, Bisphenol A, uses 84-65-1D, Anthraquinone, derivs. 86-73-7D, Fluorene, alkyl derivs., polymers 90-44-8, Anthrone 94-41-7D, Chalcone, amino substitution derivative 95-16-9, Benzothiazole 106-51-4D, Quinone, derivs. 110-02-1D, Thiofuran, oligomers 148-24-3, 8-Quinolinol, uses 198-55-0D, Perylene, derivs. 273-53-0, Benzoxazole 288-32-4, Imidazole, uses 288-42-6, Oxazole 288-88-0, 1H-1,2,4-Triazole 289-72-5D, Thiopyran, derivs. 290-37-9D, Pyrazine, styryl derivs. 486-25-9, Fluorenone 486-25-9D, Fluorenone, derivs. 588-59-0, Stilbene 919-30-2, Aminopropyltriethoxysilane 2085-33-8, Tris(8-hydroxyquinolinato)aluminum 4425-82-5, Fluorenylidene methane 7439-93-2, Lithium, uses 7439-95-4, Magnesium, uses 7440-23-5, Sodium, uses 7440-74-6, Indium, uses 9003-53-6, Polystyrene 9011-14-7, PMMA 11120-54-0, Oxadiazole 12033-89-5, Silicon nitride, uses 25038-59-9, uses 25067-59-8, Polyvinylcarbazole 25087-26-7, Polymethacrylic acid 25265-76-3, Phenylenediamine 36118-45-3, Pyrazoline 37271-44-6 39455-90-8, Pyrazolone 42559-81-9, Anthracene-styrene copolymer 60676-86-0, Silica glass 65181-78-4, TPD (photoreceptor) 96638-49-2, Polyphenylenevinylene
(organic film electrodes manufacturing with)

L68 ANSWER 6 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2005:345979 HCAPLUS Full-text
DOCUMENT NUMBER: 142:381971
TITLE: Organic electroluminescent devices employing an organometallic complex-containing layer adjacent to a reducing metal and fabrication process of electroluminescent devices
INVENTOR(S): Kido, Junji; Matsumoto, Toshio; Nakada, Takeshi; Kawamura, Norifumi
PATENT ASSIGNEE(S): International Manufacturing and Engineering Services Co., Ltd., Japan
SOURCE: Eur. Pat. Appl., 33 pp.
CODEN: EPXXDW
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

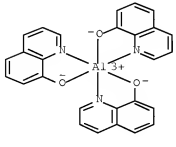
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1524707	A2	20050420	EP 2004-24611 <--	20041015
EP 1524707	A3	20060426		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK, HR				
JP 2005123094	A	20050512	JP 2003-358401 <--	20031017
CN 1610473	A	20050427	CN 2004-10080504 <--	20040930
US 20050084713	A1	20050421	US 2004-966708 <--	20041015
KR 2005037400	A	20050421	KR 2004-83343 <--	20041018

KR 858106 B1 20080910
PRIORITY APPLN. INFO.: JP 2003-358401 A 20031017
<--

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 22 Apr 2005
AB Organic electroluminescent devices are described which comprise a substrate, an anode layer; an organic structure including at least one light-emissive layer; a low resistance electron-transporting layer including a mixed layer of an electron-donating metal dopant and an organic compound; an organometallic complex-containing layer including an organometallic complex compound containing at least one metal ion selected from an alkaline metal ion, an alkaline earth metal ion and a rare earth metal ion; a reducing reaction generating layer; and a cathode layer, in that order. At least one of the anode layer and the cathode layer is transparent. The reducing reaction generating layer is a layer produced by depositing on the organometallic complex-containing layer a thermally reducible metal capable of reducing the metal ion in the organometallic complex compound in a vacuum to the corresponding metal, followed by causing an oxidation-reduction reaction between them.
IT 25387-93-3
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
RN 25387-93-3 HCAPLUS
CN 8-Quinolinol, lithium salt (1:1) (CA INDEX NAME)

● Li

IT 2085-33-8, Aluminum tris(8-hydroxyquinolinato)
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



IT 7429-90-5, Aluminum, uses
(thermally reducible metal; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

A1

IC ICM H01L051-20
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 76
IT Organometallic compounds
(alkaline earth compds.; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Organometallic compounds
(alkali metal compds.; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Sputtering
(cathode deposition by; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Vapor deposition process
(electron-beam, thermally reducible metal deposition by; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Vapor deposition process
(laser ablation, thermally reducible metal deposition by; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Electroluminescent devices
Semiconductor device fabrication
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Coordination compounds
Organometallic compounds
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)
IT Alkali metals, uses
Alkaline earth metals
Rare earth metals, uses
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal resulting in formation of)
IT Alkali metal compounds
Alkaline earth compounds
Rare earth compounds
(organometallic compds.; organic electroluminescent devices employing

organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT Organometallic compounds
(rare earth compds.; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT Vapor deposition process
(resistive heating; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT Reduction
(thermal; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 50926-11-9, Indium tin oxide
(electrode; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 123847-85-8, α-NPD
(hole-transporting layer; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 25387-93-3
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 2085-33-8, Aluminum tris(8-hydroxyquinolinato) 4733-39-5, Bathocuproine 7440-46-2, Cesium, uses
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 7439-93-2P, Lithium, uses
(organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 7429-90-5, Aluminum, uses
(thermally reducible metal; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

IT 7440-21-3, Silicon, uses 7440-32-6, Titanium, uses 7440-33-7, Tungsten, uses 7440-67-7, Zirconium, uses
(thermally reducible metal; organic electroluminescent devices employing organometallic complex-containing layer adjacent to reducing metal and fabrication process of electroluminescent devices)

OS.CITING REF COUNT: 2 THERE ARE 2 CAPLUS RECORDS THAT CITE THIS RECORD (8 CITINGS)

REFERENCE COUNT: 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 7 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN

ACCESSION NUMBER: 2005:345978 HCAPLUS Full-text

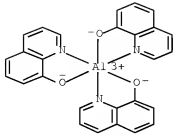
DOCUMENT NUMBER: 142:381970

TITLE: Organic electroluminescent devices employing a mixed hole injection layer of a metal oxide and an organic compound formed by co-deposition

INVENTOR(S): Kido, Junji; Matsumoto, Toshio; Nakada, Takeshi; Kawamura, Norifumi
PATENT ASSIGNEE(S): International Manufacturing and Engineering Services Co., Ltd., Japan; Mitsubishi Heavy Industries, Ltd.
SOURCE: Eur. Pat. Appl., 50 pp.
CODEN: EPXXDW
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1524706	A2	20050420	EP 2004-24610 <--	20041015
EP 1524706	A3	20060510		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK, HR				
JP 2005123095	A	20050512	JP 2003-358402 <--	20031017
CN 1610470	A	20050427	CN 2004-10080503 <--	20040930
CN 100466331	C	20090304		
KR 2005037390	A	20050421	KR 2004-82844 <--	20041015
KR 894306	B1	20090424		
US 20050084712	A1	20050421	US 2004-966251 <--	20041015
JP 2010034594	A	20100212	JP 2009-258054 <--	20091111
PRIORITY APPLN. INFO.:			JP 2003-358402 A <--	20031017

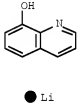
ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
OTHER SOURCE(S): MARPAT 142:381970
ED Entered STN: 22 Apr 2005
AB An organic electroluminescent device includes an anode electrode layer; a cathode electrode layer opposed to the anode electrode layer; a hole injection layer provided adjacent to the anode electrode layer an organic structure including at least one light-emissive layer or at least one light-emissive unit having at least one light-emissive layer; between the anode electrode layer and the cathode electrode layer; where at least one of the anode electrode layer and the cathode electrode layer is transparent; and the hole injection layer includes a mixed layer of a metal oxide and an organic compound formed by co-deposition.
IT 2085-33-8, Aluminum tris(8-hydroxyquinolinato)
7429-90-5, Aluminum, uses 25387-93-3
(organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

Al

RN 25387-93-3 HCAPLUS
CN 8-Quinolinol, lithium salt (1:1) (CA INDEX NAME)



Li

IC ICM H01L051-20
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 76
ST org electroluminescent device mixed hole injection oxide org layer
IT Sputtering
(anode deposition by; organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT Amines, uses
(aromatic; organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT Vapor deposition process
(electron-beam, oxide deposition using; organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT Vapor deposition process
(laser ablation, oxide deposition using; organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)

IT Electroluminescent devices
(organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT Oxides (inorganic), uses
Porphyrins
(organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT Vapor deposition process
(resistive heating; organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT 574-93-6D, Phthalocyanine, derivs. 2085-33-8, Aluminum tris(8-hydroxyquinolinato) 4733-39-5, Bathocuproine 7429-90-5, Aluminum, uses 7440-46-2, Cesium, uses 25387-93-3 50926-11-9, Indium tin oxide
(organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
IT 1314-62-1, Vanadium pentoxide, properties 1314-68-7, Rhenium oxide (Re2O7) 123847-85-8, α-NPD 185690-41-9, 2-TNATA 189363-47-1 404001-42-9
(organic electroluminescent devices employing mixed hole injection layer of metal oxide and organic compound formed by co-deposition)
OS.CITING REF COUNT: 6 THERE ARE 6 CAPLUS RECORDS THAT CITE THIS RECORD (13 CITINGS)
REFERENCE COUNT: 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 8 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2004:508931 HCAPLUS Full-text
DOCUMENT NUMBER: 141:57069
TITLE: Method of fabrication of large-area solar photovoltaic devices
INVENTOR(S): Duggal, Anil Raj; Yakimov, Aharon
PATENT ASSIGNEE(S): General Electric Company, USA
SOURCE: U.S. Pat. Appl. Publ., 13 pp.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20040118444	A1	20040624	US 2002-248140 <--	20021220
PRIORITY APPLN. INFO.:			US 2002-248140 <--	20021220

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 24 Jun 2004
AB An organic photovoltaic (PV) device comprises a plurality of organic PV cells connected in series to cover a large area. The organic PV device optionally has an elec. circuit element connected in parallel to each organic PV cell. The organic PV device allows for continued operation even when short circuits develop or elec. interruption occurs in one of the cells. The device is

conveniently manufactured using a shadow mask, which allows for the formation of several consecutive layers in one apparatus

IT 148-24-3D, 8-Hydroxyquinoline, metal complex
7429-90-5, Aluminum, uses 7440-66-6, Zinc, uses
150477-54-6, Indium tin zinc oxide
(method of fabrication of large-area solar photovoltaic devices)

RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

Al

RN 7440-66-6 HCAPLUS
CN Zinc (CA INDEX NAME)

Zn

RN 150477-54-6 HCAPLUS
CN Indium tin zinc oxide (CA INDEX NAME)

Component	Ratio	Component Registry Number
O	x	17778-80-2
In	x	7440-74-6
Zn	x	7440-66-6
Sn	x	7440-31-5

IC ICM H01L031-00
INCL 136244000; 136263000; 438080000; 438082000
CC 52-2 (Electrochemical, Radiational, and Thermal Energy Technology)
Section cross-reference(s): 76
IT Vapor deposition process
(chemical; method of fabrication of large-area solar photovoltaic devices)
IT Cyanine dyes
Diodes
Electrodeposition
Electron beam evaporation
Electron transport

Hole transport
Resistors
Semiconductor materials
Solar cells
Sputtering
Varistors
(method of fabrication of large-area solar photovoltaic devices)
IT Vapor deposition process
(phys.; method of fabrication of large-area solar photovoltaic devices)
IT Coating process
(vacuum; method of fabrication of large-area solar photovoltaic devices)
IT 81-33-4 86-74-8D, Carbazole, derivs. 91-19-0D, Quinoxaline, derivs. 91-22-5D, Quinoline, derivs. 110-86-1D, Pyridine, derivs. 120-12-7D, Anthracene, derivs. 148-24-3D, 8-Hydroxyquinoline, metal complex 198-55-0D, Perylene, derivs. 288-32-4D, Imidazole, derivs. 289-95-2D, Pyrimidine, derivs. 494-72-4D, Diphenoquinone, derivs. 519-73-3, Triphenylmethane 578-95-0, Acridone 588-59-0D, Stilbene, derivs. 603-34-9, Triphenylamine 1327-33-9, Antimony oxide 1332-29-2, Tin oxide 7429-90-5, Aluminum, uses 7439-91-0, Lanthanum, uses 7439-93-2, Lithium, uses 7439-95-4, Magnesium, uses 7440-02-0, Nickel, uses 7440-06-4, Platinum, uses 7440-09-7, Potassium, uses 7440-19-9, Samarium, uses 7440-22-4, Silver, uses 7440-23-5, Sodium, uses 7440-24-6, Strontium, uses 7440-31-5, Tin, uses 7440-39-3, Barium, uses 7440-45-1, Cerium, uses 7440-48-4, Cobalt, uses 7440-53-1, Europium, uses 7440-57-5, Gold, uses 7440-66-6, Zinc, uses 7440-67-7, Zirconium, uses 7440-70-2, Calcium, uses 7440-74-6, Indium, uses 9033-83-4, Polyphenylene 11120-54-0D, Oxadiazole, derivs. 12654-97-6, Triazine 25233-30-1, Polyaniline 25233-34-5, Polythiophene 30604-81-0, Polypyrrole 36118-45-3, Pyrazoline 37306-44-8D, Triazole, derivs. 50926-11-9, Ito 66280-99-7, Poly(thienylene vinylene) 91201-85-3, PolyIsothianaphthene 96638-49-2, Poly(phenylene vinylene) 96638-49-2D, Polyphenylene vinylene, CN- and CF3-substituted 99685-96-8, Buckminsterfullerene 150477-54-6, Indium tin zinc oxide
(method of fabrication of large-area solar photovoltaic devices)

L68 ANSWER 9 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2003:1007243 HCAPLUS Full-text
DOCUMENT NUMBER: 140:51531
TITLE: Method for the roll-to-roll deposition of an optically transparent and high conductivity metallic thin film
INVENTOR(S): He, Xiao-Ming; Heydarpour, Ramin
PATENT ASSIGNEE(S): Avery Dennison Corporation, USA
SOURCE: PCT Int. Appl., 67 pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 2
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2003107079	A2	20031224	WO 2003-US18755 <--	20030612
WO 2003107079	A9	20040304		

WO 2003107079 A3 20040701
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG
US 20040001915 A1 20040101 US 2002-172282 20020614
<--
US 6811815 B2 20041102
AU 2003259035 A1 20031231 AU 2003-259035 20030612
<--
EP 1534510 A2 20050601 EP 2003-760348 20030612
<--
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, SK
PRIORITY APPLN. INFO.: US 2002-172282 A 20020614
<--
WO 2003-US18755 W 20030612
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ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT

ED Entered STN: 26 Dec 2003

AB The invention relates to a method for the roll-to-roll deposition of an optically transparent and high conductivity metallic thin film, allowing the film to be collected in a continuous roll. The method consists of the steps of (i) providing a flexible plastic substrate; (ii) depositing a multilayered conductive metallic film on the flexible plastic substrate by a thin film deposition technique to form a composite film; and (iii) collecting the composite film in continuous rolls.

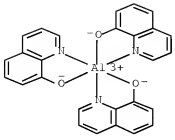
IT 148-24-3D, 8-Hydroxyquinoline, metal complexes
2085-33-8D, Alq3, derivs.
(luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

RN 148-24-3 HCAPLUS

CN 8-Quinolinol (CA INDEX NAME)

RN 2085-33-8 HCAPLUS

CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



IC ICM G02F
CC 76-2 (Electric Phenomena)
Section cross-reference(s): 38, 56, 57, 73, 78
ST roll deposition optically transparent conductive metallic thin film
IT Ketones, uses
(1,3-diketones, metal complexes, luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyesters, uses
(Arylite, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyesters, uses
(ST 504, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyesters, uses
(aromatic, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Vapor deposition process
(chemical; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Schiff bases
(complexes, luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Rolls
(composite film collected on; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Metals, uses
(conductive films; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyolefins
(cycloalkene polymer-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Films
(elec. conductive; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Electric conductors
(films; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Coating process
(flexible substrate reinforced by; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT Glass substrates
(flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Epoxy resins, uses
Fluoropolymers, uses
Phenolic resins, uses
Polycarbonates, uses
Polyimides, uses
Polyolefins
Polysulfones, uses
Polyurethanes, uses
(flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Vapor deposition process
(ion plating; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyacetylenes, uses
(ladder, luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Charge transfer complexes
Organometallic compounds
Poly(arylenealkenylenes)
Polyanilines
Polyphenyls
Rare earth complexes
(luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Composites
Laser ablation
Luminescent substances
Magnetron sputtering
(method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyalkenamers
(method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Ladder polymers
(polyacetylenes, luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyethers, uses
(polyamide-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyethers, uses
(polyester-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyamides, uses
Polyesters, uses
Polysulfones, uses
(polyether-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Cycloalkenes
(polymers, polyolefin-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)
IT Polyethers, uses

(polysulfone-, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT Gold alloy, nonbase
Silver alloy, nonbase
(method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 24968-11-4, Polyethylene naphthalate
(Kaladex S 1020/500, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 25038-59-9, ST 504, uses
(ST 504, flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 7440-21-3, Silicon, uses 9002-84-0, Polytetrafluoroethylene 9004-35-7, Cellulose acetate 9011-14-7, Polymethylmethacrylate 24937-79-9, Polyvinylidene fluoride 25014-41-9, Polyacrylonitrile 25230-87-9 25667-42-9, Polyethersulfone 150872-17-6, Arton 637005-62-0, Arton G 7810
(flexible substrate; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 91-22-5D, Quinoline, metal complexes 123-54-6D, Acetylacetone, metal complexes 148-24-3D, 8-Hydroxyquinoline, metal complexes 2085-33-8D, Alq3, derivs. 7440-31-5D, Tin, tin(IV) complexes 9033-83-4, Poly(phenylene) 17056-99-4D, 5-Hydroxyquinoxaline, metal complexes 25038-69-1, Poly(phenylacetylene) 25067-59-8, Poly(N-vinylcarbazole) 25233-30-1, Poly(aniline) 25233-34-5, Poly(thiophene) 25233-34-5D, Poly(thiophene), 3-alkyl derivs. 26009-24-5, Poly(p-phenylenevinylene) 26009-24-5D, Poly(p-phenylenevinylene), dialkoxy derivs. 41999-83-1D, Maleonitriledithiol, metal complexes 95270-88-5, Poly(fluorene) 104934-51-2, Poly(3-octylthiophene)
(luminescent material; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 7440-22-4, Silver, uses 7440-57-5, Gold, uses 25038-78-2, Dicyclopentadiene homopolymer 174351-38-3, Cerium indium oxide 246032-84-8, Copper 0.5, gold 1, silver 98.5 (atomic)
(method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

IT 7440-37-1, Argon, processes 7727-37-9, Nitrogen, processes 7782-44-7, Oxygen, processes
(sputtering process gas; method for roll-to-roll deposition of optically transparent and high conductivity metallic thin film)

REFERENCE COUNT: 1 THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 10 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN

ACCESSION NUMBER: 2003:898222 HCAPLUS Full-text
DOCUMENT NUMBER: 140:278163
TITLE: Organic electroluminescent material and its application
INVENTOR(S): Qiu, Yong; Qiao, Juan
PATENT ASSIGNEE(S): Qinghua University, Peop. Rep. China
SOURCE: Faming Zhuanli Shenqing Gongkai Shuomingshu, 26 pp.
CODEN: CNXXEV
DOCUMENT TYPE: Patent
LANGUAGE: Chinese
FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
CN 1388205	A	20030101	CN 2002-121289 <--	20020613
CN 1250674	C	20060412		
US 20040001970	A1	20040101	US 2003-352493 <--	20030128
US 7232616	B2	20070619		
JP 2004162002	A	20040610	JP 2003-168569 <--	20030613
JP 3689815	B2	20050831		

PRIORITY APPLN. INFO.: CN 2002-121289 A 20020613 <-- CN 2002-145923 A 20021023 <--

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT

OTHER SOURCE(S): MARPAT 140:278163

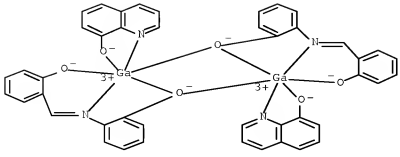
ED Entered STN: 18 Nov 2003

AB The organic electroluminescent material is a Schiff base containing tridentate complex, (L2L3M)n (L2 = bidentate ligand; L3 = schiff base-type tridentate ligand; M = metal ion such as Al, Ga, or In; and n = 1 or 2). The L3 is HOXCH:NYOH (X and/or Y = Ph, naphthyl, phenanthryl, pyridyl, thiazolyl, carbazolyl, or their derivs. substituted by alkyl, alkoxy, NO2, CN, NH2, halo, aromatic group, thienyl, pyrrolyl, or pyridyl). The L2 is HOZN [Z = 8-hydroxyquinoline, 4-hydroxy- 1,5-naphthyridine, 5-hydroxyquinoxaline, 2-(2-hydroxyphenyl)benzoxazole, 2-(2-hydroxyphenyl)benzimidazole, 2-(2-hydroxyphenyl)benzothiazole, 10-hydroxybenzo[h]quinoline, pyridine-2-carboxylic acid, or their derivs. substituted by alkyl, alkoxy, NO2, CN, NH2, halo, aromatic group, thienyl, pyrrolyl, or pyridyl]. The organic electroluminescent material is prepared by condensing salicylaldehyde or derivative with 2-aminophenol or its derivative to obtain Schiff base, complexing with M3+ salt and another ligand, and purifying via sublimation. The organic electroluminescent material may be used as electron transmission layer or luminescent layer of organic electroluminescent device with multilayer or monolayer structure, doped dye, or dye, preferably used in preparing red organic electroluminescent device. The electroluminescent devices were manufactured on ITO-modified glass sheet by vacuum vapor deposition.

IT 502844-08-8P
(crystal structure of; organic electroluminescent material for electroluminescent device)

RN 502844-08-8 HCAPLUS

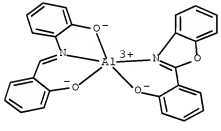
CN Gallium, bis[μ-[2-[[[2-(hydroxy-κO:κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]]bis(8-quinolinolato-κN1,κO8)di-, stereoisomer (9CI) (CA INDEX NAME)



IT 326850-13-9P 656823-73-3P 656823-77-7P
656823-83-5P 656823-85-7P 656823-86-8P
656823-94-8P 656824-04-3P 656824-10-1P
656824-12-3P 674768-96-8P 674768-98-0P
674769-00-7P 674769-01-8P 674769-03-0P
(organic electroluminescent material for electroluminescent device)

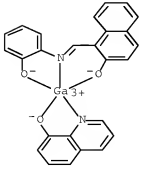
RN 326850-13-9 HCAPLUS

CN Aluminum, [2-(2-benzoxazolyl-κN3)phenolato-κO][2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)

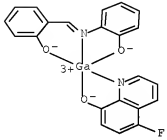


RN 656823-73-3 HCAPLUS

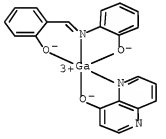
CN Gallium, [1-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-2-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



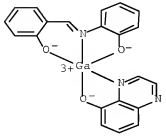
RN 656823-77-7 HCAPLUS
CN Gallium, (5-fluoro-8-quinolinolato-κN1,κO8)[2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



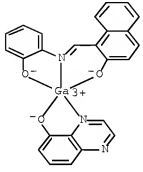
RN 656823-83-5 HCAPLUS
CN Gallium, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](1,5-naphthyridin-4-olato-κN5,κO4)- (9CI) (CA INDEX NAME)



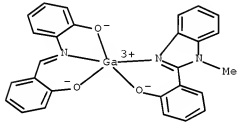
RN 656823-85-7 HCAPLUS
CN Gallium, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](5-quinoxalinolato-κN4,κO5)- (9CI) (CA INDEX NAME)



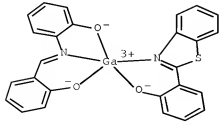
RN 656823-86-8 HCAPLUS
CN Gallium, [1-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-2-naphthalenolato(2-)-κO](5-quinoxalinolato-κN4,κO5)-(CA INDEX NAME)



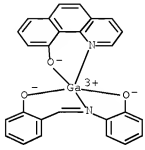
RN 656823-94-8 HCAPLUS
CN Gallium, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO][2-(1-methyl-1H-benzimidazol-2-yl-κN3)phenolato-κO]- (9CI) (CA INDEX NAME)



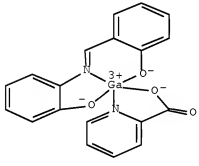
RN 656824-04-3 HCAPLUS
CN Gallium, [2-(2-benzothiazolyl-κN3)phenolato-κO][2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



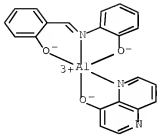
RN 656824-10-1 HCAPLUS
CN Gallium, (benzo[h]quinolin-10-olato-κN1,κO10)[2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



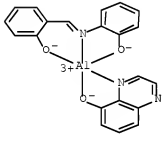
RN 656824-12-3 HCAPLUS
CN Gallium, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](2-pyridinecarboxylato-κN1,κO2)- (9CI) (CA INDEX NAME)



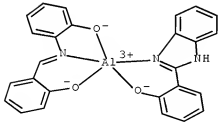
RN 674768-96-8 HCAPLUS
CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](1,5-naphthyridin-4-olato-κN5,κO4)- (9CI) (CA INDEX NAME)



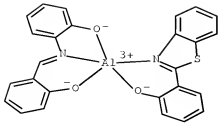
RN 674768-98-0 HCAPLUS
CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](5-quinoxalinolato-κN4,κO5)- (9CI) (CA INDEX NAME)



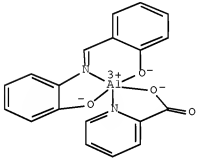
RN 674769-00-7 HCAPLUS
CN Aluminum, [2-(1H-benzimidazol-2-yl-κN3)phenolato-κO][2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



RN 674769-01-8 HCAPLUS
CN Aluminum, [2-(2-benzothiazolyl-κN3)phenolato-κO][2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



RN 674769-03-0 HCAPLUS
CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](2-pyridinecarboxylato-κN1,κO2)- (9CI) (CA INDEX NAME)



IT 148-24-3, 8-Hydroxyquinoline, reactions 7446-70-0, Aluminum chloride, reactions 13450-90-3, Gallium trichloride
(preparation of organic electroluminescent material)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 7446-70-0 HCAPLUS
CN Aluminum chloride (AlCl3) (CA INDEX NAME)

RN 13450-90-3 HCAPLUS
CN Gallium chloride (GaCl3) (CA INDEX NAME)

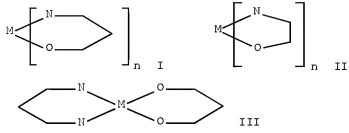
IC ICM C09K011-06
CC 73-5 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 74, 75
IT 502844-08-8P
(crystal structure of; organic electroluminescent material for electroluminescent device)
IT 326850-13-9P 656823-73-3P 656823-77-7P
656823-83-5P 656823-85-7P 656823-86-8P
656823-94-8P 656824-04-3P 656824-10-1P
656824-12-3P 674768-95-7P 674768-96-8P
674768-97-9P 674768-98-0P 674768-99-1P
674769-00-7P 674769-01-8P 674769-02-9P
674769-03-0P
(organic electroluminescent material for electroluminescent device)
IT 90-02-8, Salicylaldehyde, reactions 95-55-6, 2-Aminophenol
98-98-6, Pyridine-2-carboxylic acid 148-24-3,
8-Hydroxyquinoline, reactions 387-97-3, 5-Fluoro-8-hydroxyquinoline
708-06-5, 2-Hydroxy-1-naphthaldehyde 835-64-3,
2-(2-Hydroxyphenyl)benzoxazole 2963-66-8,
2-(2-Hydroxyphenyl)benzimidazole 3411-95-8,
2-(2-Hydroxyphenyl)benzothiazole 5423-54-1,
4-Hydroxy-1,5-naphthyridine 7446-70-0, Aluminum chloride,
reactions 10025-82-8, Indium chloride 13450-90-3,
Gallium trichloride 17056-99-4, 5-Hydroxyquinoxaline 33155-90-7,
10-Hydroxybenzo[h]quinoline
(preparation of organic electroluminescent material)
OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS)

L68 ANSWER 11 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2003:433000 HCAPLUS Full-text
DOCUMENT NUMBER: 139:14916
TITLE: Electrophotographic photoreceptors with charge-stopping layers containing metal complexes and their manufacture
INVENTOR(S): Fukumoto, Koichi; Aragae, Ryuichi; Ono, Masayuki
PATENT ASSIGNEE(S): Matsushita Electric Industrial Co., Ltd., Japan
SOURCE: Jpn. Kokai Tokkyo Koho, 13 pp.
CODEN: JKXXAF
DOCUMENT TYPE: Patent
LANGUAGE: Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003162079	A	20030606	JP 2001-358780 <--	20011126

PRIORITY APPLN. INFO.: JP 2001-358780 20011126
<--

OTHER SOURCE(S): MARPAT 139:14916
ED Entered STN: 06 Jun 2003
GI



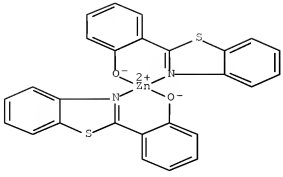
I II III

AB The photoreceptor comprises a conductive support, a charge-stopping layer containing metal complex I, II, or III (M = metal ion; n = 0, 1, 2, 3), a charge-generating layer, and a charge-transfer layer. Specific compds. suitable as ligand for the complexes are also given. Manufacture of the photoreceptor includes vacuum vapor deposition of the complex. Clear electrophotog. images free of fogging are obtained even after repeated use.

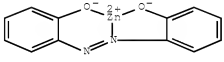
IT 148-24-3DP, 8-Hydroxyquinoline, metal complexes
58280-31-2P 116083-83-1P 164259-44-3P
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)

RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

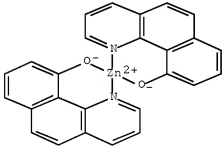
RN 58280-31-2 HCAPLUS
CN Zinc, bis[2-(2-benzothiazolyl-κN3)phenolato-κO]-, (T-4)-
(CA INDEX NAME)



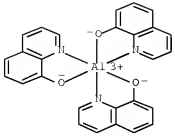
RN 116083-83-1 HCAPLUS
CN Zinc, [[2,2'-(azo-κN)bis[phenolato-κO]](2-)]- (9CI) (CA INDEX NAME)



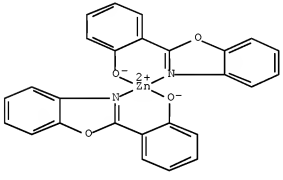
RN 164259-44-3 HCAPLUS
CN Zinc, bis(benzo[h]quinolin-10-olato-κN1,κO10)-, (T-4)- (CA INDEX NAME)



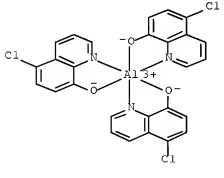
IT 2085-33-8, Tris(8-quinolinolato)aluminum
23467-27-8 41584-66-1 78970-14-6
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)
RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



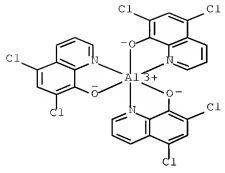
RN 23467-27-8 HCAPLUS
CN Zinc, bis[2-(2-benzoxazolyl-κN3)phenolato-κO]-, (T-4)-
(CA INDEX NAME)



RN 41584-66-1 HCAPLUS
CN Aluminum, tris(5-chloro-8-quinolinolato-κN1,κO8)- (CA
INDEX NAME)



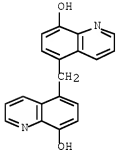
RN 78970-14-6 HCAPLUS
CN Aluminum, tris(5,7-dichloro-8-quinolinolato-κN1,κO8)- (CA
INDEX NAME)



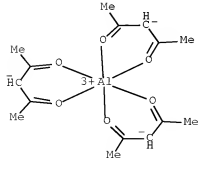
IC ICM G03G005-14
ICS G03G005-00; G03G005-06
CC 74-3 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
ST electrophotog photoreceptor charge stopping layer metal complex
IT Electrophotographic photoconductors (photoreceptors)
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)
IT Chelates
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)
IT Vapor deposition process
(vacuum; electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)
IT 66-71-7DP, 1,10-Phenanthroline, metal complexes 148-24-3DP, 8-Hydroxyquinoline, metal complexes 835-64-3DP, metal complexes 2050-14-8DP, metal complexes 3411-95-8DP, metal complexes 17904-83-5P, Tris(dibenzoylmethanato)(1,10-phenanthroline)europium 18130-95-5P, Tris(benzoylacetonato)(1,10-phenanthroline)europium 33155-90-7DP, 10-Hydroxybenzo[h]quinoline, metal complexes 33421-36-2DP, metal complexes 58280-31-2P 116083-83-1P 164259-44-3P
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)
IT 2085-33-8, Tris(8-quinolinolato)aluminum 23467-27-8 41584-66-1 78970-14-6
(electrophotog. photoreceptors with metal complex charge-stopping layers formed by vacuum vapor deposition)

L68 ANSWER 12 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2001:644372 HCAPLUS Full-text
DOCUMENT NUMBER: 135:378318
TITLE: Organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film
AUTHOR(S): Yu, J.; Chen, Z.; Miyata, S.

CORPORATE SOURCE: Tokyo University of Agriculture and Technology, Graduate School of Bio-Applications and Systems Engineering (BASE), Tokyo, Koganei, 184-0012, Japan
SOURCE: Synthetic Metals (2001), 123(2), 239-243
CODEN: SYMEDZ; ISSN: 0379-6779
PUBLISHER: Elsevier Science S.A.
DOCUMENT TYPE: Journal
LANGUAGE: English
ED Entered STN: 04 Sep 2001
AB In this paper CVD method is presented for the preparation of chelate polymer film as constituent for organic electroluminescent (EL) devices. The chelate polymer film, poly(bis(8-hydroxy-5-quinolyl)methane Al), was thermally converted into by simultaneously coevapd. Al acetylacetonate and bis(8-hydroxy-5-quinolyl)-methane in the gas phase in the CVD process. Two kinds of EL devices using the chelate polymer as the emitting material were fabricated, and their EL properties were characterized and discussed.
IT 2536-71-2 13963-57-0, Aluminum acetylacetonate
(organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
RN 2536-71-2 HCAPLUS
CN 8-Quinolinol, 5,5'-methylenebis- (CA INDEX NAME)

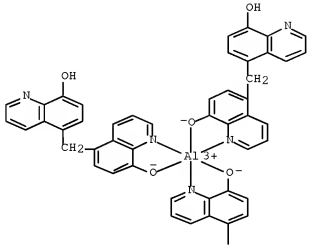


RN 13963-57-0 HCAPLUS
CN Aluminum, tris(2,4-pentanedionato-κO2,κO4)-, (OC-6-11)-
(CA INDEX NAME)



IT 374067-48-8
(polymeric; organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
RN 374067-48-8 HCAPLUS
CN Aluminum, tris[5-[(8-hydroxy-5-quinolinyl)methyl]-8-quinolinolato-κN1,κO8]- (CA INDEX NAME)

PAGE 1-A



PAGE 2-A

CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
IT Vapor deposition process
(chemical; organic electroluminescent device fabricated with chem. vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
IT Electroluminescent devices
IR spectra
Luminescence
(organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane

aluminum chelate polymer film)
IT 25067-59-8, PVK
(organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
IT 2536-71-2 13963-57-0, Aluminum acetylacetonate
(organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
IT 374067-48-8
(polymeric; organic electroluminescent device fabricated with chemical vapor deposited bis(8-hydroxy-5-quinolyl)-methane aluminum chelate polymer film)
OS.CITING REF COUNT: 5 THERE ARE 5 CAPLUS RECORDS THAT CITE THIS RECORD (5 CITINGS)
REFERENCE COUNT: 18 THERE ARE 18 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 13 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2001:582229 HCAPLUS Full-text
DOCUMENT NUMBER: 135:160002
TITLE: Organic electroluminescent device and its manufacturing method
INVENTOR(S): Sato, Yoshiharu; Tanamura, Mitsuru
PATENT ASSIGNEE(S): Mitsubishi Chemical Corp., Japan
SOURCE: PCT Int. Appl., 46 pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2001058222	A1	20010809	WO 2001-JP719 <--	20010201
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
JP 2001332390	A	20011130	JP 2001-18792 <--	20010126
JP 3972584	B2	20070905		
EP 1173049	A1	20020116	EP 2001-902728 <--	20010201
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
US 20020037429	A1	20020328	US 2001-968500 <--	20011002
US 6534202	B2	20030318		
PRIORITY APPLN. INFO.:			JP 2000-25515 <--	A 20000202
			JP 2000-76620	A 20000317

<--
WO 2001-JP719 W 20010201
<--

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT

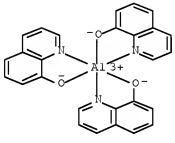
ED Entered STN: 10 Aug 2001

AB An organic electroluminescent device comprises a luminescence layer interposed between a pos. electrode and a neg. electrode on a substrate. The neg. electrode comprises metal material, alkaline metal, and C and O atoms. The neg. electrode is formed by vapor phase deposition using a metal material and an organic compound containing an alkaline metal. The organic electroluminescent device is heat-resistant and weather-resistant, and it operates on low voltage and emits high-luminance light while maintaining stable luminescence characteristics. The organic electroluminescent element has a wide range of manufacturing process conditions.

IT 2085-33-8, Al 8q 37220-89-6D, Aluminum lithium oxide, carbon doped 157077-25-3
(organic electroluminescent device)

RN 2085-33-8 HCAPLUS

CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



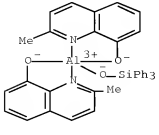
RN 37220-89-6 HCAPLUS

CN Aluminum lithium oxide (CA INDEX NAME)

Component	Ratio	Component Registry Number
O	x	17778-80-2
Li	x	7439-93-2
Al	x	7429-90-5

RN 157077-25-3 HCAPLUS

CN Aluminum, bis(2-methyl-8-quinolinolato-κN1,κO8)(triphenylsilanolato)- (CA INDEX NAME)



IT 7429-90-5, Aluminum, uses 25387-93-3
(organic electroluminescent device)
RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

Al

RN 25387-93-3 HCAPLUS
CN 8-Quinolinol, lithium salt (1:1) (CA INDEX NAME)

Li

IC H05B033-26; H05B033-10; H05B033-14
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
Section cross-reference(s): 74
IT Vapor deposition process
(manufacture of organic electroluminescent device)
IT 147-14-8, Copper phthalocyanine 2085-33-8, Al 8q
37220-89-6D, Aluminum lithium oxide, carbon doped
50926-11-9, ITO 58328-31-7 94928-86-6 123847-85-8,
4,4'-Bis[N-[1-naphthyl]-N-phenylamino]biphenyl 157077-25-3
(organic electroluminescent device)
IT 1313-59-3, Sodium oxide, uses 7429-90-5, Aluminum, uses
12057-24-8, Lithium oxide, uses 25387-93-3 26134-62-3,
Lithium nitride 160883-74-9 352521-14-3
(organic electroluminescent device)
OS.CITING REF COUNT: 7 THERE ARE 7 CAPLUS RECORDS THAT CITE THIS RECORD (7 CITINGS)
REFERENCE COUNT: 14 THERE ARE 14 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 14 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2001:185142 HCAPLUS Full-text
DOCUMENT NUMBER: 134:246046
TITLE: Efficient electron-injection for organic electroluminescent devices
INVENTOR(S): Madathil, Joseph K.; Mason, Max Garrett; Tang, Ching Wan
PATENT ASSIGNEE(S): Eastman Kodak Company, USA
SOURCE: Eur. Pat. Appl., 12 pp.

CODEN: EPXXDW
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1083612	A2	20010314	EP 2000-202921 <--	20000821
EP 1083612	A3	20040102		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
US 6278236	B1	20010821	US 1999-387402 <--	19990902
JP 2001085165	A	20010330	JP 2000-267679 <--	20000904
PRIORITY APPLN. INFO.:			US 1999-387402 <--	A 19990902

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 16 Mar 2001
AB An organic electroluminescent (EL) device having a layered structure, including an anode; an organic hole-transport layer in contact with the anode; an organic emitting layer having 1 surface thereof in contact with the hole-transport layer; an organic electron-transport layer in contact with a second surface of the emitting layer; an electron-injecting layer in contact with the electron-transport layer; and a cathode in contact with the electron-injecting layer, in which the electron-injecting layer includes Al and ≥1 alkali halide or ≥1 alkaline earth halide.
IT 7429-90-5, Aluminum, processes
(electron-injection layer; efficient electron-injection layers for organic electroluminescent devices)
RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

Al

IT 148-24-3, 8-Quinolinol, processes
(emitting layer; efficient electron-injection layers for organic electroluminescent devices)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

IT 37275-76-6, Aluminum Zinc oxide 117944-65-7, Indium Zinc oxide
(light transmissive anode; efficient electron-injection

layers for organic electroluminescent devices)
RN 37275-76-6 HCAPLUS
CN Aluminum zinc oxide (CA INDEX NAME)

Component	Ratio	Component Registry Number
O	x	17778-80-2
Zn	x	7440-66-6
Al	x	7429-90-5

RN 117944-65-7 HCAPLUS
CN Indium zinc oxide (CA INDEX NAME)

Component	Ratio	Component Registry Number
O	x	17778-80-2
In	x	7440-74-6
Zn	x	7440-66-6

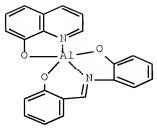
IC ICM H01L051-20
CC 76-3 (Electric Phenomena)
Section cross-reference(s): 74, 75
IT Electron transport
Electron-hole recombination
Hole transport
(efficient electron-injection layers for organic electroluminescent devices)
IT Transparent films
(elec. conductive, anode; efficient electron-injection layers for organic electroluminescent devices)
IT Alkali metal fluorides
Alkaline earth fluorides
(electron-injection layer; efficient electron-injection layers for organic electroluminescent devices)
IT Conduction electrons
(electron-injection; efficient electron-injection layers for organic electroluminescent devices)
IT Electric conductors
(films, transparent, anode; efficient electron-injection layers for organic electroluminescent devices)
IT Electroluminescent devices
(organic; efficient electron-injection layers for organic electroluminescent devices)
IT Glass, uses
Plastics, uses
(substrate; efficient electron-injection layers for organic electroluminescent devices)
IT Vapor deposition process
(vacuum; efficient electron-injection layers for organic electroluminescent devices)
IT 7429-90-5, Aluminum, processes
(electron-injection layer; efficient electron-injection layers for organic electroluminescent devices)
IT 7681-49-4, Sodium fluoride, processes 7783-40-6, Magnesium fluoride 7783-48-4, Strontium fluoride 7787-32-8, Barium fluoride 7789-23-3, Potassium fluoride 7789-24-4, Lithium fluoride, processes 7789-75-5, Calcium fluoride, processes 13400-13-0, Cesium fluoride 13446-74-7, Rubidium fluoride

(electron-injection layers; efficient electron-injection layers for organic electroluminescent devices)
IT 148-24-3, 8-Quinolinol, processes
(emitting layer; efficient electron-injection layers for organic electroluminescent devices)
IT 1332-29-2, Tin oxide 12640-79-8, Nickel tungsten oxide 37275-76-6, Aluminum Zinc oxide 50926-11-9, Indium-tin-oxide 56997-34-3, Cadmium tin oxide 117944-65-7, Indium Zinc oxide 158346-28-2, Indium Magnesium oxide
(light transmissive anode; efficient electron-injection layers for organic electroluminescent devices)
IT 14808-60-7, Quartz, uses
(substrate; efficient electron-injection layers for organic electroluminescent devices)
OS.CITING REF COUNT: 6 THERE ARE 6 CAPLUS RECORDS THAT CITE THIS RECORD (6 CITINGS)
REFERENCE COUNT: 1 THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L68 ANSWER 15 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2001:162141 HCAPLUS Full-text
DOCUMENT NUMBER: 134:185709
TITLE: Organic electroluminescent materials
INVENTOR(S): Qiu, Yong; Shao, Yan
PATENT ASSIGNEE(S): Qinghua Univ., Peop. Rep. China
SOURCE: Faming Zhuanli Shenqing Gongkai Shuomingshu, 18 pp.
CODEN: CNXXEV
DOCUMENT TYPE: Patent
LANGUAGE: Chinese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
CN 1258710	A	20000705	CN 2000-100040 <--	20000107
CN 1139649	C	20040225		
US 20010037024	A1	20011101	US 2001-755688 <--	20010105
US 6410766	B1	20020625		
PRIORITY APPLN. INFO.:			CN 2000-100040 A <--	20000107

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
ED Entered STN: 08 Mar 2001
GI



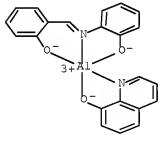
I

AB The electroluminescent materials compose of Al complexes having organic ligands such as 8-hydroxyquinoline and Schiff base from salicylaldehyde and o-aminophenol, i.e., I, and/or their fused naphtho derivs. and analogs. The electroluminescent material is synthesized by condensing salicylaldehyde with o-aminophenol or derivs., recrystg. in organic solvent to obtain Schiff base as ligand, and complexing with Al compound and 8-hydroxyquinoline or 2-phenol in the presence of a base. The electroluminescent element containing I was manufactured by chemical vapor deposition and vacuum electroplating method and it showed superior brightness.

IT 303981-53-5P 326850-12-8P 326850-13-9P
326850-14-0P 326850-15-1P 326850-16-2P
326850-17-3P 326850-18-4P 326850-19-5P
326850-20-8P 326850-21-9P
(preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)

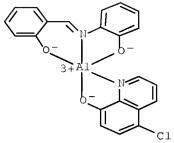
RN 303981-53-5 HCAPLUS

CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO](8-quinolinolato-κN1,κO8)- (9CI) (CA INDEX NAME)

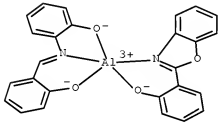


RN 326850-12-8 HCAPLUS

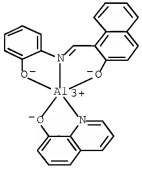
CN Aluminum, (5-chloro-8-quinolinolato-κN1,κO8)[2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



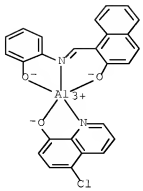
RN 326850-13-9 HCAPLUS
CN Aluminum, [2-(2-benzoxazolyl-κN3)phenolato-κO][2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]phenolato(2-)-κO]- (9CI) (CA INDEX NAME)



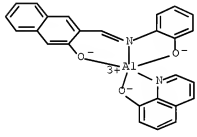
RN 326850-14-0 HCAPLUS
CN Aluminum, [1-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-2-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



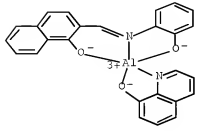
RN 326850-15-1 HCAPLUS
CN Aluminum, (5-chloro-8-quinolinolato-κN1,κO8)[1-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-2-naphthalenolato(2-)-κO]- (CA INDEX NAME)



RN 326850-16-2 HCAPLUS
CN Aluminum, [3-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-2-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)-
(CA INDEX NAME)

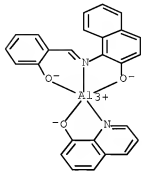


RN 326850-17-3 HCAPLUS
CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]imino-κN]methyl]-1-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)-
(CA INDEX NAME)



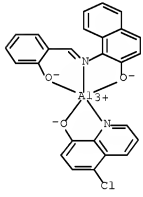
RN 326850-18-4 HCAPLUS

CN Aluminum, [1-[[[2-(hydroxy-κO)phenyl]methylene]amino-κN]-2-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)-(CA INDEX NAME)



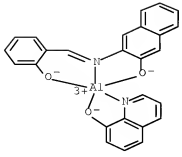
RN 326850-19-5 HCAPLUS

CN Aluminum, (5-chloro-8-quinolinolato-κN1,κO8)[1-[[[2-(hydroxy-κO)phenyl]methylene]amino-κN]-2-naphthalenolato(2-)-κO]- (CA INDEX NAME)

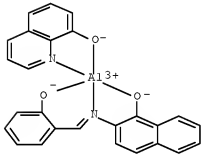


RN 326850-20-8 HCAPLUS

CN Aluminum, [3-[[[2-(hydroxy-κO)phenyl]methylene]amino-κN]-2-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)-(CA INDEX NAME)

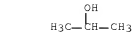


RN 326850-21-9 HCAPLUS
CN Aluminum, [2-[[[2-(hydroxy-κO)phenyl]methylene]amino-κN]-1-naphthalenolato(2-)-κO](8-quinolinolato-κN1,κO8)-
(CA INDEX NAME)



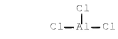
IT 148-24-3, 8-Hydroxyquinoline, reactions 555-31-7
, Triisopropoxyaluminum 7446-70-0, Aluminum chloride, reactions
(preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

RN 555-31-7 HCAPLUS
CN 2-Propanol, aluminum salt (3:1) (CA INDEX NAME)



1/3 Al

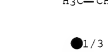
RN 7446-70-0 HCAPLUS
CN Aluminum chloride (AlCl3) (CA INDEX NAME)



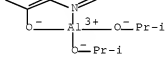
IC C09K011-06
CC 73-5 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
IT Vapor deposition process
(chemical; preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)
IT Electroluminescent devices
(thin-film; preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)
IT 303981-53-5P 326850-12-8P 326850-13-9P
326850-14-0P 326850-15-1P 326850-16-2P
326850-17-3P 326850-18-4P 326850-19-5P
326850-20-8P 326850-21-9P
(preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)
IT 90-02-8, Salicylaldehyde, reactions 95-55-6, 2-Aminophenol
130-16-5, 5-Chloro-8-hydroxyquinoline 148-24-3,
8-Hydroxyquinoline, reactions 555-31-7,
Triisopropoxyaluminum 581-71-5,
3-Hydroxy-2-naphthalenecarboxaldehyde 708-06-5,
2-Hydroxy-1-naphthalenecarboxaldehyde 835-64-3 2834-92-6,
1-Amino-2-naphthol 7446-70-0, Aluminum chloride, reactions
(preparation of quinolinolatoaluminum complexes as organic electroluminescent materials)
OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS)

L68 ANSWER 16 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 2000:222672 HCAPLUS Full-text
DOCUMENT NUMBER: 133:12007
TITLE: Preparation and characterization of some alumosiloxanes as single-source MOCVD precursors for aluminosilicate coatings
AUTHOR(S): Zemskova, S. M.; Haynes, J. A.; Besmann, T. M.; Hunt, R. D.; Beach, D. B.; Golovlev, V. N.
CORPORATE SOURCE: Oak Ridge National Laboratory, Oak Ridge, TN, 37831-6063, USA
SOURCE: Journal de Physique IV: Proceedings (2000), 10(Pr2, Chemical Vapour Deposition), Pr2/35-Pr2/42

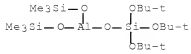
CODEN: JPICEI; ISSN: 1155-4339
PUBLISHER: EDP Sciences
DOCUMENT TYPE: Journal
LANGUAGE: English
ED Entered STN: 07 Apr 2000
AB Alumosiloxanes [Al(OSiMe3)3]2, (Me3SiO)2Al[OSi(OBu-t)3], [(acac)Al(OSiMe3)2]2, (Ox)Al[OSi(OBu-t)3]2, (Me = CH3; Bu-t = t-Bu; acac = C5H7O2; Ox = C9H6NO) were synthesized and their thermal properties were studied by TGA in Ar at 25-500°. [Al(OSiMe3)3]2 and [(acac)Al(OSiMe3)2]2 showed substantial volatility during heating regardless of their dimeric structures in the solid state, while the other compds. were largely decomposed under the same conditions. Therefore, [Al(OSiMe3)3]2 and [(acac)Al(OSiMe3)2]2 were chosen as prospective precursors for the MOCVD of aluminosilicate coatings. Study of these compds. by laser mass-spectrometry (laser excitation at 355 nm) showed that the decomposition pathway proceeds through the formation of a number of heavy species originating from dimeric [>Al<(OSi)2>Al<] fragments of [Al(OSiMe3)3]2 and [(acac)Al(OSiMe3)2]2 mols. and Si-containing light species of m/z 52 (C2Si) and 55(C2H3Si) originating from OSiMe3 ligands. Initial expts. were carried out on the deposition of aluminosilicate coatings on Si carbide from the precursors described.
IT 555-31-7, Aluminum triisopropoxide
(for preparation of alumosiloxanes)
RN 555-31-7 HCAPLUS
CN 2-Propanol, aluminum salt (3:1) (CA INDEX NAME)



IT 15710-92-6P
(preparation and reaction with tri(t-butyl)siloxane)
RN 15710-92-6 HCAPLUS
CN Aluminum, bis(2-propanolato)(8-quinolinolato-κN1,κO8)-, (T-4)- (CA INDEX NAME)

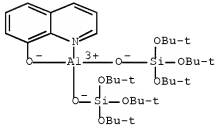


IT 270903-75-8P 270903-76-9P
(preparation and thermal decomposition as potential solvent assisted MOCVD precursor for aluminosilicate coatings)
RN 270903-75-8 HCAPLUS
CN Aluminum, bis(trimethylsilanolato)[tris(1,1-dimethylethyl) orthosilicato-κO''']- (9CI) (CA INDEX NAME)



RN 270903-76-9 HCAPLUS

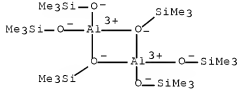
CN Aluminum, (8-quinolinolato-κN1,κO8)bis[tris(1,1-dimethylethyl) orthosilicato-κO''']-, (T-4)- (9CI) (CA INDEX NAME)



IT 20009-02-3P 92784-84-4P
(preparation, laser mass spectra and thermal decomposition as potential single-source MOCVD precursor for aluminosilicate coatings)

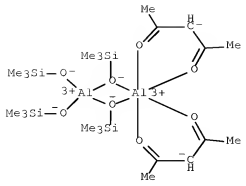
RN 20009-02-3 HCAPLUS

CN Aluminum, bis[μ-(trimethylsilanolato)]tetrakis(trimethylsilanolato)di- (8CI, 9CI) (CA INDEX NAME)



RN 92784-84-4 HCAPLUS

CN Aluminum, bis(2,4-pentanedionato-κO,κO')bis[μ-(trimethylsilanolato)]bis(trimethylsilanolato)di- (9CI) (CA INDEX NAME)



IT 148-24-3, 8-Hydroxyquinoline, reactions
(reaction with aluminum triisopropoxide)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

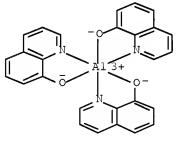
CC 78-7 (Inorganic Chemicals and Reactions)
IT Mass spectra
(laser; of alumosiloxanes as potential MOCVD precursors for aluminosilicate coatings)
IT Vapor deposition process
(metalorg.; preparation and characterization of alumosiloxanes as potential MOCVD precursors for aluminosilicate coatings)
IT Thermal decomposition
(of alumosiloxanes as potential MOCVD precursors for aluminosilicate coatings)
IT 107-46-0, Hexamethyldisiloxane 123-54-6, Acetylacetone, reactions
555-31-7, Aluminum triisopropoxide 2754-27-0,
Trimethylacetoxysilane 5356-87-6, Tri(tert-butoxy)silane
(for preparation of alumosiloxanes)
IT 15710-92-6P
(preparation and reaction with tri(t-butyl)siloxane)
IT 270903-75-8P 270903-76-9P
(preparation and thermal decomposition as potential solvent assisted MOCVD precursor for aluminosilicate coatings)
IT 20009-02-3P 92784-84-4P
(preparation, laser mass spectra and thermal decomposition as potential single-source MOCVD precursor for aluminosilicate coatings
)
IT 148-24-3, 8-Hydroxyquinoline, reactions
(reaction with aluminum triisopropoxide)
OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS)
REFERENCE COUNT: 14 THERE ARE 14 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE

RE FORMAT

L68 ANSWER 17 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 1995:547736 HCAPLUS Full-text
DOCUMENT NUMBER: 123:69921
ORIGINAL REFERENCE NO.: 123:12237a,12240a
TITLE: Manufacture of organic electroluminescent device
INVENTOR(S): Sato, Yoshiharu; Kanai, Hiroyuki
PATENT ASSIGNEE(S): Mitsubishi Kagaku KK, Japan
SOURCE: Jpn. Kokai Tokkyo Koho, 8 pp.
CODEN: JKXXAF
DOCUMENT TYPE: Patent
LANGUAGE: Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 07062526	A	19950307	JP 1993-205375 <--	19930819
PRIORITY APPLN. INFO.:			JP 1993-205375 <--	19930819

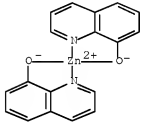
ED Entered STN: 13 May 1995
AB The device is manufactured by forming the organic light-emitting layer on a substrate at 60-150°. The layer may contain a metal complex of 8-hydroxyquinoline, which may be formed by vacuum vapor deposition. The device shows good heat resistance and emission stability for long periods.
IT 2085-33-8, Tris(8-hydroxyquinolinato)aluminum
7069-05-8 13978-85-3,
Bis(8-hydroxyquinolinato)zinc 14642-34-3,
Tris(8-hydroxyquinolinato)gallium
(manufacture of electroluminescent device containing hydroxyquinoline metal complex)
RN 2085-33-8 HCAPLUS
CN Aluminum, tris(8-quinolinolato-κN1,κO8)- (CA INDEX NAME)



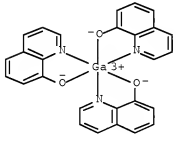
RN 7069-05-8 HCAPLUS
CN 8-Quinolinol, calcium salt (2:1) (CA INDEX NAME)

●1/2 Ca

RN 13978-85-3 HCAPLUS
CN Zinc, bis(8-quinolinolato-κN1,κO8)-, (T-4)- (CA INDEX NAME)



RN 14642-34-3 HCAPLUS
CN Gallium, tris(8-quinolinolato-κN1,κO8)- (9CI) (CA INDEX NAME)



IC ICM C23C014-24
ICS C09K011-06; H05B033-10; H05B033-14
CC 73-11 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)
ST electroluminescent device hydroxyquinoline metal complex; deposition vacuum vapor electroluminescent film
IT Electroluminescent devices
Vapor deposition processes
(manufacture of electroluminescent device containing hydroxyquinoline metal complex)
IT 2085-33-8, Tris(8-hydroxyquinolinato)aluminum
7069-05-8 13978-85-3,

Bis(8-hydroxyquinolinato)zinc 14514-42-2,
Tris(8-hydroxyquinolinato)indium 14642-34-3,
Tris(8-hydroxyquinolinato)gallium 15276-55-8 15956-38-4,
Tris(8-hydroxyquinolinato)scandium 16009-78-2,
Tris(8-hydroxyquinolinato)yttrium 67952-28-7,
Bis(8-hydroxyquinolinato)magnesium
(manufacture of electroluminescent device containing hydroxyquinoline metal complex)
OS.CITING REF COUNT: 1 THERE ARE 1 CAPLUS RECORDS THAT CITE THIS RECORD (1 CITINGS)

L68 ANSWER 18 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 1992:85311 HCAPLUS Full-text
DOCUMENT NUMBER: 116:85311
ORIGINAL REFERENCE NO.: 116:14527a,14530a
TITLE: Forming highly anticorrosive thin films
INVENTOR(S): Minowa, Emiko; Kobayashi, Shiro; Ito, Masahiko; Izumitani, Masakiyo
PATENT ASSIGNEE(S): Hitachi, Ltd., Japan
SOURCE: Jpn. Kokai Tokkyo Koho, 8 pp.
CODEN: JKXXAF
DOCUMENT TYPE: Patent
LANGUAGE: Japanese
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 03111553	A	19910513	JP 1989-247947 <--	19890926
JP 06021343	B	19940323		
PRIORITY APPLN. INFO.:			JP 1989-247947 <--	19890926

ED Entered STN: 06 Mar 1992
AB The title process involves covering a substrate with a metal and an organic compound forming a compound insol. with the metal by elec. discharge in vacuo. Making magnetic disks, magnetic heads, optomagnetic disks, and electrolytic condensers is also claimed. A polyethylene substrate was treated with Co-Ni and dimethylglyoxime by magnetron sputter process at 1 + 10-3 Pa vacuum.
IT 148-24-3, 8-Hydroxyquinoline, uses
(sputter coating with metals and, for highly anticorrosive thin film formation)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

IT 7429-90-5, Aluminum, uses
(sputter coating with organic compds. and, for highly anticorrosive thin film formation)
RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

A1

IC ICM C23C014-06
ICS C23C014-12; G11B005-85; G11B007-26; H01G009-05
CC 38-3 (Plastics Fabrication and Uses)
Section cross-reference(s): 42
ST sputter coating metal org compd; anticorrosive thin film sputter coating; magnetic disk sputter coating; head magnetic sputter coating; optomagnetic disk sputter coating; elec condenser sputter coating ; cobalt nickel sputter coating; dimethylglyoxime sputter coating; polyethylene sputter coating
IT Sputtering
(coating by, of metal and organic compds.)
IT Electric capacitors
(manufacture of, sputter coating in)
IT Recording apparatus
(magnetic heads, manufacture of, sputter coating in)
IT Memory devices
(magnetic, disks, manufacture of, sputter coating in)
IT Optical imaging devices
(magneto-, disks, manufacture of, sputter coating in)
IT Recording apparatus
(optical disks, manufacture of, sputter coating in)
IT 9002-88-4P, Polyethylene
(formation of highly anticorrosive metal-organic compound thin films on, by sputter coating)
IT 66-71-7, o-Phenanthroline 72-48-0D, Alizarin, derivs. 91-20-3, Naphthalene, uses 91-20-3D, Naphthalene, derivs. 95-45-4, Dimethylglyoxime 148-24-3, 8-Hydroxyquinoline, uses 366-18-7, 2,2'-Dipyridine 463-56-9D, Thiocyanic acid, organic derivs. 13408-62-3D, Ferricyanide, organic derivs. 13408-63-4D, Ferrocyanide, organic derivs. 27598-85-2, Aminophenol
(sputter coating with metals and, for highly anticorrosive thin film formation)
IT 7429-90-5, Aluminum, uses 7439-89-6, Iron, uses 7440-02-0, Nickel, uses 7440-25-7, Tantalum, uses 7440-27-9, Terbium, uses 7440-48-4, Cobalt, uses 7440-67-7, Zirconium, uses 11101-13-6
(sputter coating with organic compds. and, for highly anticorrosive thin film formation)

L68 ANSWER 19 OF 19 HCAPLUS COPYRIGHT 2010 ACS on STN
ACCESSION NUMBER: 1984:59650 HCAPLUS Full-text
DOCUMENT NUMBER: 100:59650
ORIGINAL REFERENCE NO.: 100:8997a,9000a
TITLE: Metallic image production, and composite material and treatment solutions for this process
INVENTOR(S): Sasa, Nobumasa
PATENT ASSIGNEE(S): Konishiroku Photo Industry Co., Ltd. , Japan
SOURCE: Ger. Offen., 50 pp.
CODEN: GWXXBX
DOCUMENT TYPE: Patent
LANGUAGE: German
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 3241980	A1	19830526	DE 1982-3241980 <--	19821112
JP 58083846	A	19830519	JP 1981-181747 <--	19811114
JP 01045896	B	19891005		
JP 58083843	A	19830519	JP 1981-181748 <--	19811114
JP 01045897	B	19891005		
JP 58083847	A	19830519	JP 1981-181749 <--	19811114
US 4455364	A	19840619	US 1982-439427 <--	19821105
GB 2113152	A	19830803	GB 1982-32192 <--	19821111
GB 2113152	B	19860917		
GB 2156088	A	19851002	GB 1984-28641 <--	19841113
GB 2156088	B	19861126		
GB 2155861	A	19851002	GB 1984-28642 <--	19841113
PRIORITY APPLN. INFO.:			JP 1981-181747 A <--	19811114
			JP 1981-181748 A <--	19811114
			JP 1981-181749 A <--	19811114
			GB 1982-32192 A3 <--	19821111

ASSIGNMENT HISTORY FOR US PATENT AVAILABLE IN LSUS DISPLAY FORMAT
OTHER SOURCE(S): MARPAT 100:59650
ED Entered STN: 12 May 1984
AB Metal images having outstanding edge sharpness in the etched segments are prepared from a composite material consisting of a support, a thin metal layer, a photosensitive resin layer, and ≥1 layer containing a metal chelating agent. The metal chelating agent may also be contained in a processing solution Thus, a poly(ethylene terephthalate) support was coated with an 800 Å layer of Al by vapor deposition and then with a composition containing methacrylic acid-styrene copolymer 5, pentaerythritol triacrylate 5, 2-isopropylthioxanthone 1, diethylaminoisoamyl benzoate 0.5 g, and Me cellosolve 100 mL to give a photosensitive layer. The resultant material was then imagewise exposed to a halftone original and developed in a 25° solution containing NaOH 4, Na anthraquinone-2,6-disulfonate (I) 10 g, and water 1 L for 30 s to show no scum formation and an excellent image corresponding the original. A control which used a developer containing no I showed heavy scum formation.
IT 12252-30-1
(photoimaging composition containing layer of, for metal image production)
RN 12252-30-1 HCAPLUS
CN Aluminum, compd. with iron (2:1) (CA INDEX NAME)

Component	Ratio	Component Registry Number
Fe	1	7439-89-6
Al	2	7429-90-5

IT 7429-90-5, uses and miscellaneous
(photoimaging composition with layer of, for metal image production)
RN 7429-90-5 HCAPLUS
CN Aluminum (CA INDEX NAME)

Al

IT 148-24-3, uses and miscellaneous
(photoimaging compns. containing, for metal image production)
RN 148-24-3 HCAPLUS
CN 8-Quinolinol (CA INDEX NAME)

IC G03F007-00
CC 74-10 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
IT 64-02-8 100-51-6, uses and miscellaneous 853-68-9 1310-73-2, uses and miscellaneous 7664-38-2, uses and miscellaneous 7705-08-0, uses and miscellaneous 61702-43-0
(developer compns. containing, for metal layer-containing photoimaging composition)
IT 853-67-8
(developer compns. containing, for metal layer-containing photoimaging compns.)
IT 7440-69-9, uses and miscellaneous 12252-30-1
(photoimaging composition containing layer of, for metal image production)
IT 7429-90-5, uses and miscellaneous
(photoimaging composition with layer of, for metal image production)
IT 56-40-6, uses and miscellaneous 56-41-7, uses and miscellaneous 56-84-8, uses and miscellaneous 56-86-0, uses and miscellaneous 59-31-4 60-00-4, uses and miscellaneous 66-71-7 72-48-0 78-90-0 81-61-8 82-48-4 82-49-5 84-48-0 84-49-1 86-95-3 87-69-4, uses and miscellaneous 90-02-8, uses and miscellaneous 92-27-3 99-57-0 107-15-3, uses and miscellaneous 110-15-6, uses and miscellaneous 111-40-0 116-63-2 117-14-6 121-88-0 123-54-6, uses and miscellaneous 130-22-3 139-13-9 141-82-2, uses and miscellaneous 142-73-4 144-62-7, uses and miscellaneous 147-85-3, uses and miscellaneous 148-24-3, uses and miscellaneous 366-18-7 482-54-2 552-16-9 607-34-1 625-75-2 1787-61-7 1939-36-2 2066-93-5 2150-60-9 2466-09-3 3618-58-4 6975-60-6 10380-08-2 25149-61-5 66675-89-6 88544-95-0 88651-71-2
(photoimaging compns. containing, for metal image production)
OS.CITING REF COUNT: 4 THERE ARE 4 CAPLUS RECORDS THAT CITE THIS

RECORD (4 CITINGS)

REFERENCE COUNT: 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

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=> d his nofile

     (FILE 'HOME' ENTERED AT 09:37:24 ON 05 MAR 2010)

     FILE 'HCAPLUS' ENTERED AT 09:37:36 ON 05 MAR 2010
                E BIS(HYDROXY-5-QUNOLYL)METHANE
L1             1 SEA SPE=ON  ABB=ON  PLU=ON  US20070190247/PN
                SEL RN

     FILE 'REGISTRY' ENTERED AT 09:38:12 ON 05 MAR 2010
L2            20 SEA SPE=ON  ABB=ON  PLU=ON  (1333-74-0/BI OR 15318-08-8/BI
                OR 19553-62-9/BI OR 20791-15-5/BI OR 310888-77-8/BI OR
                310888-80-3/BI OR 310888-81-4/BI OR 310888-82-5/BI OR
                310888-85-8/BI OR 310888-87-0/BI OR 7358-26-1/BI OR
                7440-37-1/BI OR 7440-59-7/BI OR 75-24-1/BI OR 7727-37-9/BI
                OR 870126-56-0/BI OR 870126-57-1/BI OR 870126-58-2/BI OR
                870126-59-3/BI OR 97-93-8/BI)

     FILE 'HCAPLUS' ENTERED AT 09:42:18 ON 05 MAR 2010
L3             0 SEA SPE=ON  ABB=ON  PLU=ON  "BIS(HYDROXY-5-QUNOLYL)METHANE"


     FILE 'REGISTRY' ENTERED AT 09:52:12 ON 05 MAR 2010
                E C19H17N2O2/MF
L4            86 SEA SPE=ON  ABB=ON  PLU=ON  C19H17N2O2/MF
L5             0 SEA SPE=ON  ABB=ON  PLU=ON  L4 AND HYDROXYQUIN?
L6            20 SEA SPE=ON  ABB=ON  PLU=ON  L4 AND QUIN?
                E C19H14N2O2/MF
L7          1182 SEA SPE=ON  ABB=ON  PLU=ON  C19H14N2O2/MF
L8             1 SEA SPE=ON  ABB=ON  PLU=ON  L7 AND  HYDROXYQUIN?
L9            24 SEA SPE=ON  ABB=ON  PLU=ON  L7 AND 8-QUIN?
L10           11 SEA SPE=ON  ABB=ON  PLU=ON  L9 AND QUINOLINOL?
L11           10 SEA SPE=ON  ABB=ON  PLU=ON  L10 NOT  1H-INDOLE?
                E 8-HYDROXYQUINOLINATE/CN
L12            1 SEA SPE=ON  ABB=ON  PLU=ON  8-HYDROXYQUINOLINATE/CN
                E 8-HYDROXYQUINOLINOL/CN
                E 8-HYDROXYQUINOLINE/CN
L13            1 SEA SPE=ON  ABB=ON  PLU=ON  8-HYDROXYQUINOLINE/CN
L14          685 SEA SPE=ON  ABB=ON  PLU=ON  148-24-3/CRN
L15            9 SEA SPE=ON  ABB=ON  PLU=ON  16582-16-4/CRN
L16            0 SEA SPE=ON  ABB=ON  PLU=ON  856949-35-4/CRN
L17            0 SEA SPE=ON  ABB=ON  PLU=ON  848290-21-1/CRN
L18            0 SEA SPE=ON  ABB=ON  PLU=ON  444149-04-6 /CRN
L19            0 SEA SPE=ON  ABB=ON  PLU=ON  128500-72-1/CRN
L20            0 SEA SPE=ON  ABB=ON  PLU=ON  97970-36-0 /CRN
L21            2 SEA SPE=ON  ABB=ON  PLU=ON  63969-39-1/CRN
L22            1 SEA SPE=ON  ABB=ON  PLU=ON  61924-02-5/CRN
L23            0 SEA SPE=ON  ABB=ON  PLU=ON  13292-19-8/CRN
L24            0 SEA SPE=ON  ABB=ON  PLU=ON  13222-06-5/CRN
L25           34 SEA SPE=ON  ABB=ON  PLU=ON  2536-71-2/CRN
L26       664194 SEA SPE=ON  ABB=ON  PLU=ON  (AL OR GA OR ZN)/ELS
L27       122588 SEA SPE=ON  ABB=ON  PLU=ON  L26 AND CCS/CI
L28       541606 SEA SPE=ON  ABB=ON  PLU=ON  L26 NOT L27
L29       541606 SEA SPE=ON  ABB=ON  PLU=ON  L28 OR L28
                D 300000 RN
L30       300000 SEA RAN=(173475-42-8) SPE=ON  ABB=ON  PLU=ON  L28 OR L28
L31       241606 SEA SPE=ON  ABB=ON  PLU=ON  L29 NOT L30
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     FILE 'HCAPLUS' ENTERED AT 10:03:34 ON 05 MAR 2010
L32            30 SEA SPE=ON  ABB=ON  PLU=ON  L12
L33         10124 SEA SPE=ON  ABB=ON  PLU=ON  L13
L34          1839 SEA SPE=ON  ABB=ON  PLU=ON  L14
L35             3 SEA SPE=ON  ABB=ON  PLU=ON  L21
L36             7 SEA SPE=ON  ABB=ON  PLU=ON  L25
L37            60 SEA SPE=ON  ABB=ON  PLU=ON  L11
L38        143270 SEA SPE=ON  ABB=ON  PLU=ON  L27
L39        140282 SEA SPE=ON  ABB=ON  PLU=ON  L30
L40       2256613 SEA SPE=ON  ABB=ON  PLU=ON  L31
L41          2571 SEA SPE=ON  ABB=ON  PLU=ON  (L32 OR L33 OR L34 OR L35 OR
                  L36 OR L37) AND (L38 OR L39 OR L40)
L42                QUE SPE=ON  ABB=ON  PLU=ON  CHEMICAL VAPOR DEPOSIT? OR
                   CHEMICAL VAPOUR DEPOSIT? OR CVP OR VAPOR DEPOSIT? OR
                   VAPOUR DEPOSIT?
L43            27 SEA SPE=ON  ABB=ON  PLU=ON  L41 AND L42
                  E VAPOR DEPOSITION PROCESS/CT
L44        247082 SEA SPE=ON  ABB=ON  PLU=ON  "VAPOR DEPOSITION PROCESS"+PFT,
                  NT/CT
L45            28 SEA SPE=ON  ABB=ON  PLU=ON  L41 AND L44
L46            31 SEA SPE=ON  ABB=ON  PLU=ON  L43 OR L45
L47                QUE SPE=ON  ABB=ON  PLU=ON  FILM? OR THINFILM? OR LAYER?
                   OR OVERLAY? OR OVERLAID? OR LAMIN? OR LAMEL? OR (MULTILAYER
                   ?) OR SHEET? OR LEAF? OR FOIL? OR COAT? OR TOPCOAT? OR
                   OVERCOAT? OR VENEER? OR SHEATH? OR COVER? OR ENVELOP? OR
                   ENCAS? OR ENWRAP? OR OVERSPREAD?
L48            30 SEA SPE=ON  ABB=ON  PLU=ON  L46 AND L47
L49           130 SEA SPE=ON  ABB=ON  PLU=ON  (L32 OR L33 OR L34 OR L35 OR
                  L36 OR L37)(5A)L47
L50             5 SEA SPE=ON  ABB=ON  PLU=ON  L49 AND L42
L51             5 SEA SPE=ON  ABB=ON  PLU=ON  L50 AND L41
L52            30 SEA SPE=ON  ABB=ON  PLU=ON  L48 OR (L50 OR L51)
L53            18 SEA SPE=ON  ABB=ON  PLU=ON  L52 AND (1840-2006)/PRY,AY,PY
L54           565 SEA SPE=ON  ABB=ON  PLU=ON  L41 AND L47
L55            27 SEA SPE=ON  ABB=ON  PLU=ON  L54 AND L44
L56             0 SEA SPE=ON  ABB=ON  PLU=ON  L55 NOT L52
L57            16 SEA SPE=ON  ABB=ON  PLU=ON  L55 AND (1840-2006)/PRY,AY,PY

     FILE 'REGISTRY' ENTERED AT 10:30:36 ON 05 MAR 2010
L58            16 SEA SPE=ON  ABB=ON  PLU=ON  L2 AND M/ELS

     FILE 'HCAPLUS' ENTERED AT 10:31:06 ON 05 MAR 2010
L59         23254 SEA SPE=ON  ABB=ON  PLU=ON  L58
L60          1415 SEA SPE=ON  ABB=ON  PLU=ON  L59 AND L42
L61          1210 SEA SPE=ON  ABB=ON  PLU=ON  L60 AND L47
L62             1 SEA SPE=ON  ABB=ON  PLU=ON  L61 AND (L32 OR L33 OR L34 OR
                  L35 OR L36 OR L37)
L63             1 SEA SPE=ON  ABB=ON  PLU=ON  L60 AND (L32 OR L33 OR L34 OR
                  L35 OR L36 OR L37)
L64            49 SEA SPE=ON  ABB=ON  PLU=ON  L59 AND (L32 OR L33 OR L34 OR
                  L35 OR L36 OR L37)
L65             1 SEA SPE=ON  ABB=ON  PLU=ON  L64 AND L42
L66            19 SEA SPE=ON  ABB=ON  PLU=ON  L53 OR L62 OR L63 OR L65
L67             0 SEA SPE=ON  ABB=ON  PLU=ON  L57 NOT L66
L68            19 SEA SPE=ON  ABB=ON  PLU=ON  L66 OR L57
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